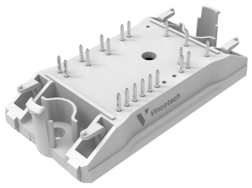
V23990-P849-C48-PM
datasheet

***flow*PIM 0** **1200 V / 8 A**

Features

- 2 Clips housing in 12 mm height
- Trench Fieldstop Technology IGBT4

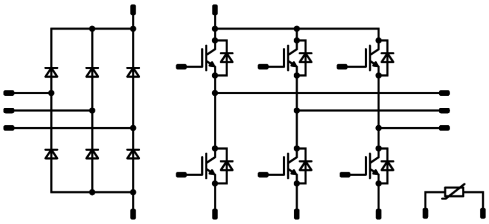
flow 0 12 mm housing



Target applications

- Industrial Drives

Schematic



Types

- V23990-P849-C48-PM

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$ T_s = 80 °C	16	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	24	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	61	W
Gate-emitter voltage	V_{GES}		±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 800 V T_j = 150 °C	10	µs
Maximum junction temperature	T_{jmax}		175	°C
Inverter Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ T_s = 80 °C	19	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	46	W
Maximum junction temperature	T_{jmax}		175	°C
Rectifier Diode				
Peak repetitive reverse voltage	V_{RRM}		1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ T_s = 80 °C	35	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms T_j = 150 °C	200	A
Surge current capability	I^2t		200	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	44	W
Maximum junction temperature	T_{jmax}		150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	**Symbol**	**Conditions**	**Value**	**Unit**
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…+(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage t_p = 1 min	2500	V
Creepage distance			>12,7	mm
Clearance			9,29	mm
Comparative Tracking Index	CTI		≥ 200	

*100 % tested in production

Characteristic Values

Parameter	**Symbol**	**Conditions**					**Values**			**Unit**
			V_{GE} **[V]** V_{GS} **[V]**	V_{CE} **[V]** V_{DS} **[V]** V_{F} **[V]**	I_{C} **[A]** I_{D} **[A]** I_{F} **[A]**	T_j **[°C]**	**Min**	**Typ**	**Max**	
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00015	25	5,3	5,8	6,3	V
Collector-emitter saturation voltage	V_{CEsat}		15		8	25 125	1,58	1,87 2,21	2,07^(1)^	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			1	µA
Gate-emitter leakage current	I_{GES}		20	0		25			120	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		490		pF
Reverse transfer capacitance	C_{res}							30		pF
Gate charge	Q_g	V_{CC} = 960 V	15		8	25		53		nC
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,57		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 32 Ω R_{goff} = 32 Ω	±15	600	8	25 125		71,4 70,6		ns
Rise time	t_r					25 125		18,6 22,8		ns
Turn-off delay time	$t_{d(off)}$					25 125		194,4 236,4		ns
Fall time	t_f					25 125		78,46 108,16		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,885 µC Q_{rFWD}=1,57 µC				25 125		0,499 0,748		mWs
Turn-off energy (per pulse)	E_{off}					25 125		0,435 0,624		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_{F} [V]	I_{C} [A] I_{D} [A] I_{F} [A]	T_{j} [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_{F}				10	25 150	1,35	1,85 1,77	2,05(1)	V
Reverse leakage current	I_{R}	V_{r} = 1200 V				25			2,7	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,07		K/W
Dynamic										
Peak recovery current	I_{RRM}	d*i*/d*t*=452 A/µs d*i*/d*t*=399 A/µs	±15	600	8	25 125		8,46 9,88		A
Reverse recovery time	t_{rr}					25 125		250,51 382,73		ns
Recovered charge	Q_{r}					25 125		0,885 1,57		µC
Reverse recovered energy	E_{rec}					25 125		0,345 0,634		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125		83,99 69,05		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Rectifier Diode										
Static										
Forward voltage	V_F				8	25 125 150		0,976 0,879 0,85	1,21(1) 1,1(1)	V
Reverse leakage current	I_R	V_r = 1600 V				25			50	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,59		K/W
Thermistor										
Static										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P							5		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

(1) Value at chip level

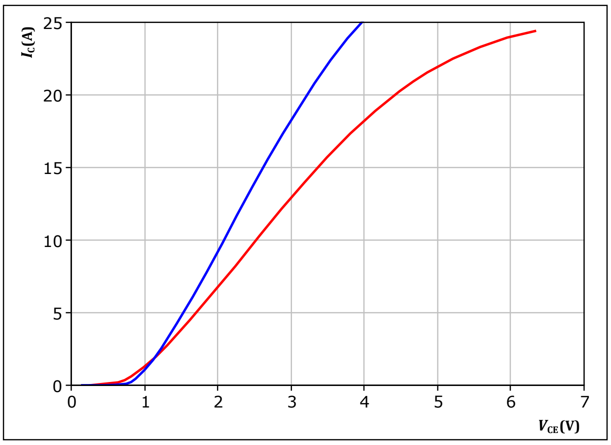
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



t_p = 250 μs

V_{GE} = 15 V

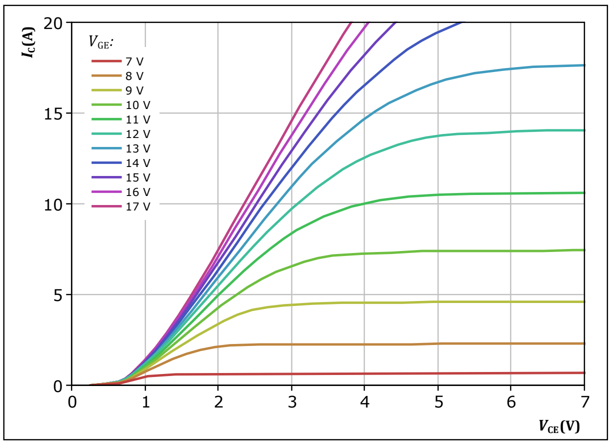
T_j: 25 °C

125 °C

figure 2. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



t_p = 250 μs

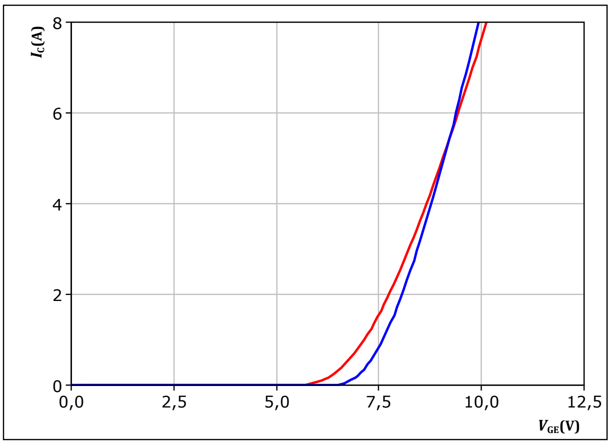
T_j = 125 °C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})



t_p = 250 μs

V_{CE} = 10 V

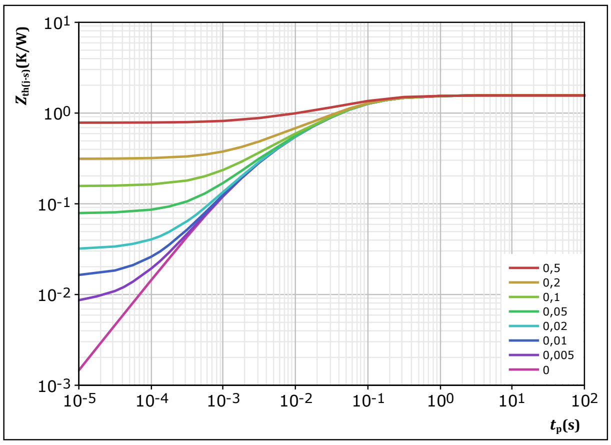
T_j: 25 °C

125 °C

figure 4. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,566 K/W

IGBT thermal model values

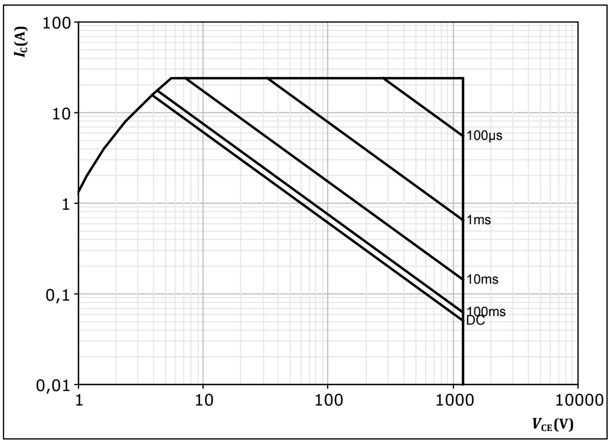
R (K/W)	τ (s)
1,42E-01	5,98E-01
6,32E-01	7,71E-02
3,98E-01	2,43E-02
2,86E-01	6,16E-03
1,08E-01	1,44E-03

Inverter Switch Characteristics

figure 5. **IGBT**

Safe operating area

I_C = f(V_{CE})



D = single pulse

T_s = 80 °C

V_{GE} = 15 V

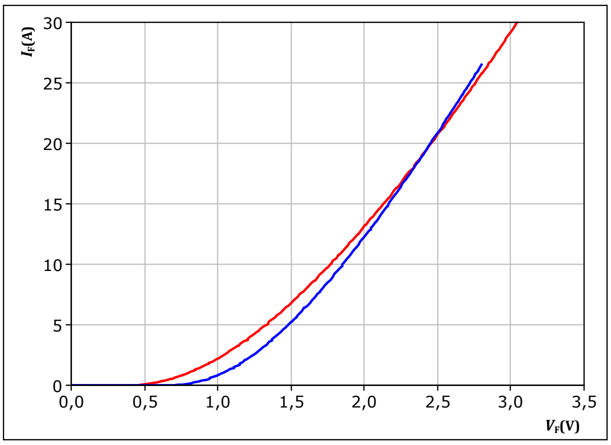
T_j = T_{jmax}

Inverter Diode Characteristics

figure 6. **FWD**

Typical forward characteristics

I_F = f(V_F)



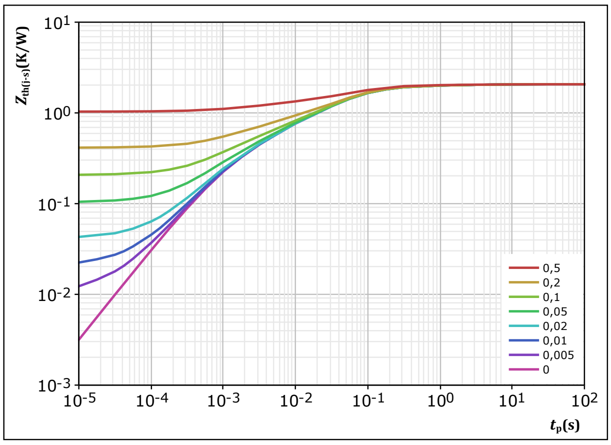
t_p = 250 µs

T_j: 25 °C 150 °C

figure 7. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 2,066 K/W

FWD thermal model values

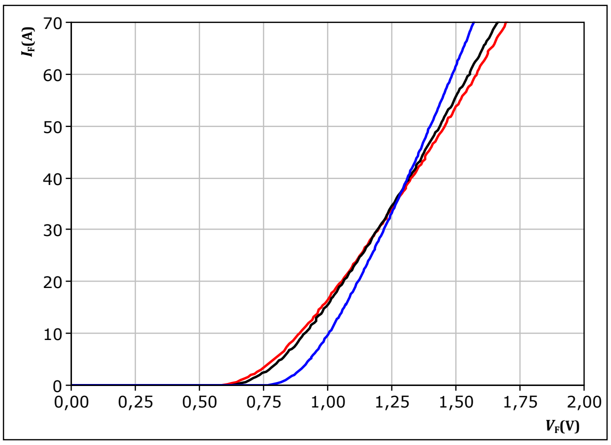
R (K/W)	τ (s)
5,09E-02	4,26E+00
1,55E-01	5,03E-01
7,75E-01	7,89E-02
5,33E-01	2,68E-02
3,54E-01	5,03E-03
1,97E-01	9,09E-04

Rectifier Diode Characteristics

figure 8. **Rectifier**

Typical forward characteristics

I_F = f(V_F)



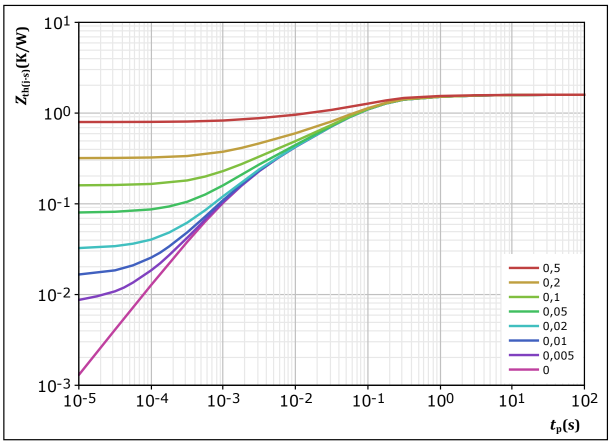
t_p = 250 µs

T_j:
- 25 °C
- 125 °C
- 150 °C

figure 9. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,594 K/W

Rectifier thermal model values

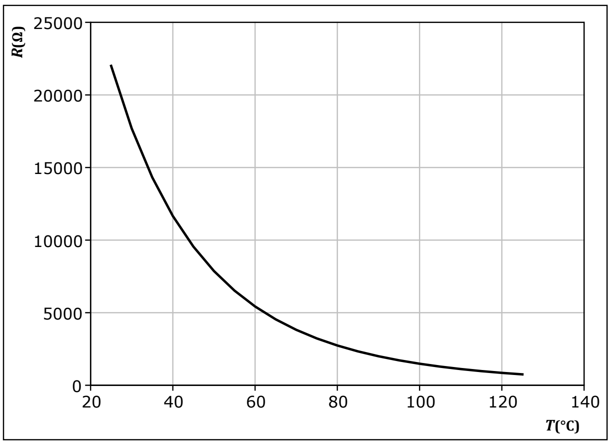
R (K/W)	τ (s)
3,44E-02	9,66E+00
1,12E-01	1,22E+00
5,81E-01	1,45E-01
4,89E-01	5,05E-02
2,38E-01	9,26E-03
1,22E-01	1,79E-03
1,81E-02	7,88E-04

Thermistor Characteristics

figure 10. **Thermistor**

Typical NTC characteristic as function of temperature

$R_T = f(T)$

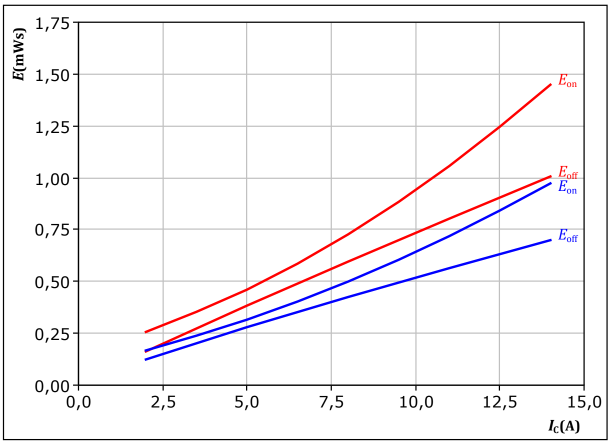


Inverter Switching Characteristics

figure 11. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



With an inductive load at

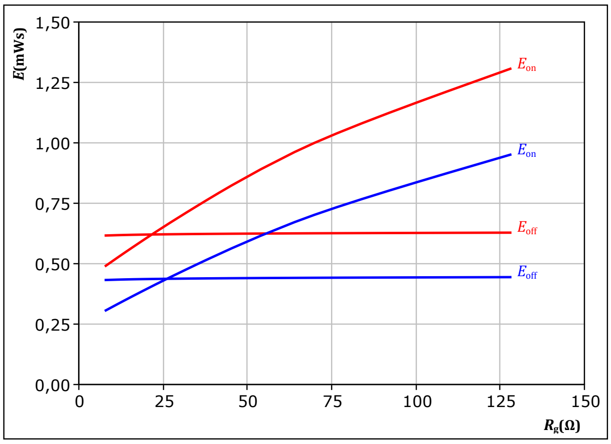
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 32 Ω
R_{goff} = 32 Ω

T_j: 25 °C
125 °C

figure 12. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



With an inductive load at

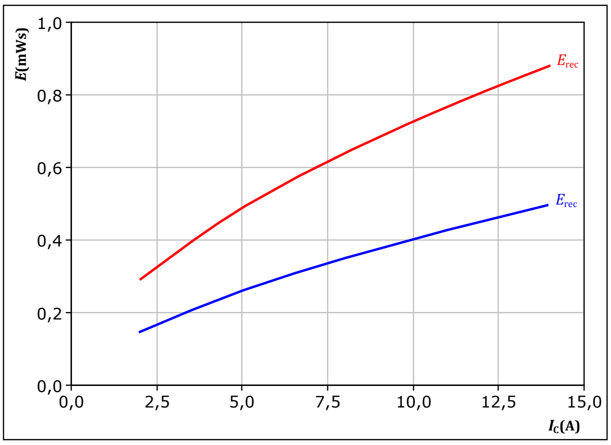
V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 8 A

T_j: 25 °C
125 °C

figure 13. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



With an inductive load at

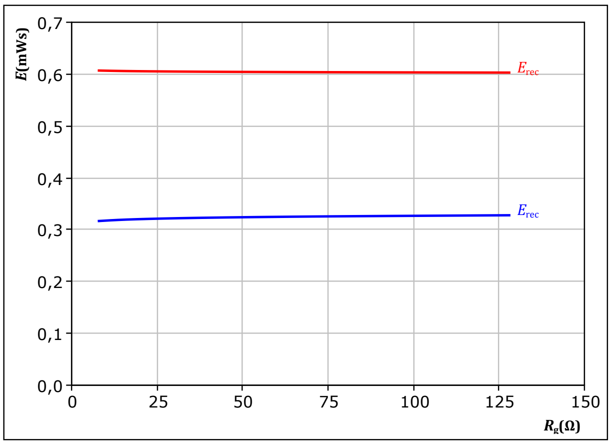
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 32 Ω

T_j: 25 °C
125 °C

figure 14. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 8 A

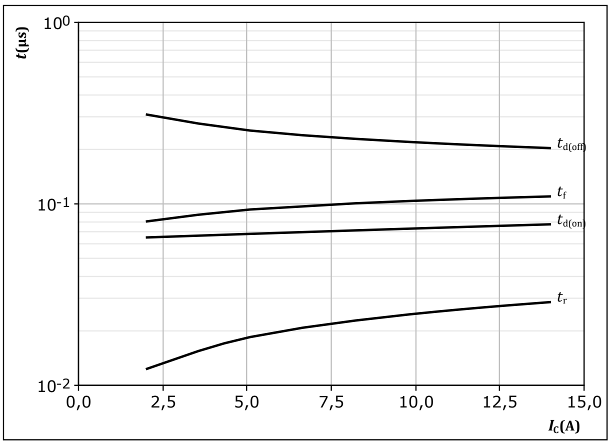
T_j: 25 °C
125 °C

Inverter Switching Characteristics

figure 15. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



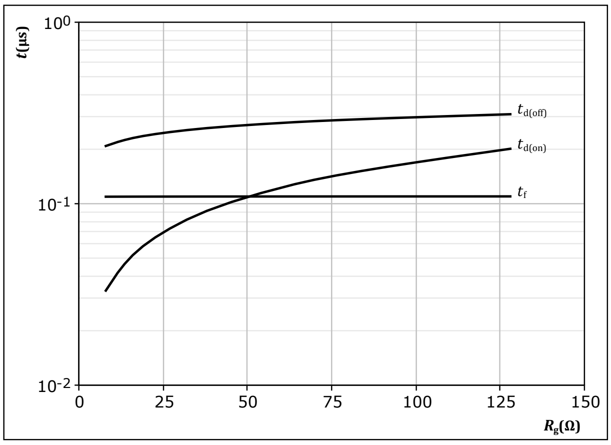
With an inductive load at

T_j = 125 °C
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 32 Ω
R_{goff} = 32 Ω

figure 16. **IGBT**

Typical switching times as a function of gate resistor

t = f(R_g)



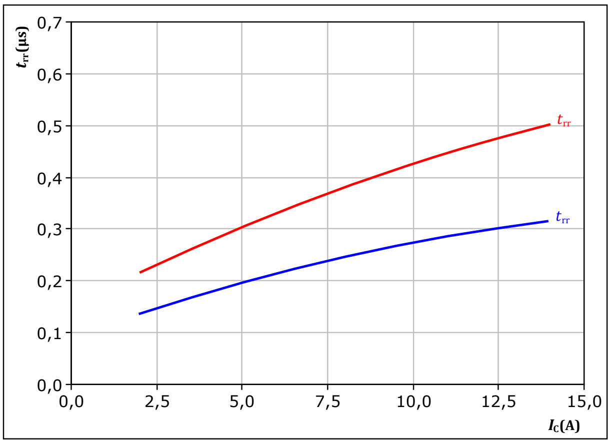
With an inductive load at

T_j = 125 °C
V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 8 A

figure 17. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

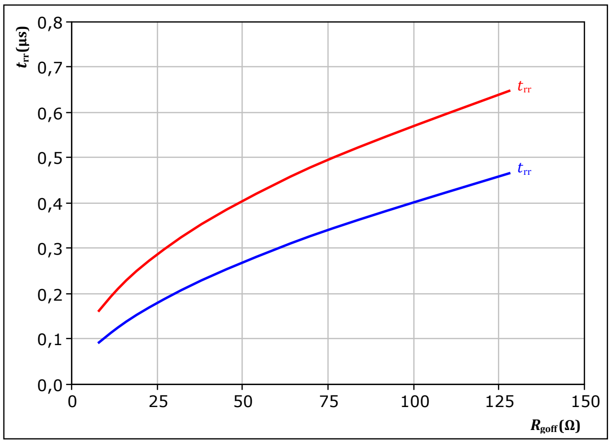
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 32 Ω

T_j:
— 25 °C
— 125 °C

figure 18. **FWD**

Typical reverse recovery time as a function of IGBT turn off gate resistor

t_{rr} = f(R_{goff})



With an inductive load at

V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 8 A

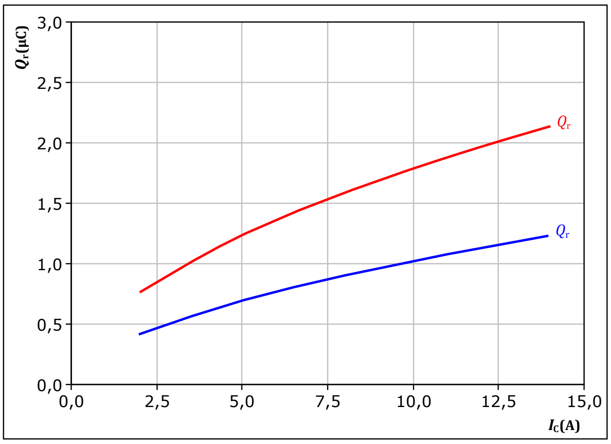
T_j:
— 25 °C
— 125 °C

Inverter Switching Characteristics

figure 19. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



With an inductive load at

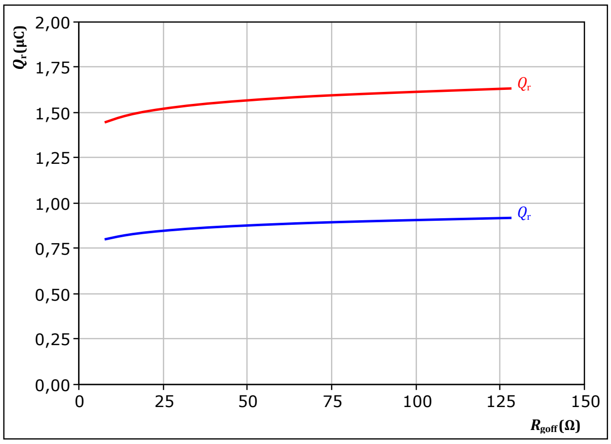
T_j:
— 25 °C
— 125 °C

V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 32 Ω

figure 20. **FWD**

Typical recovered charge as a function of turn off gate resistor

Q_r = f(R_{goff})



With an inductive load at

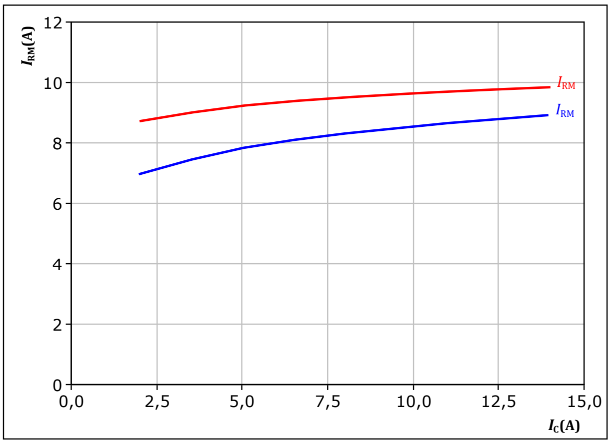
T_j:
— 25 °C
— 125 °C

V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 8 A

figure 21. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



With an inductive load at

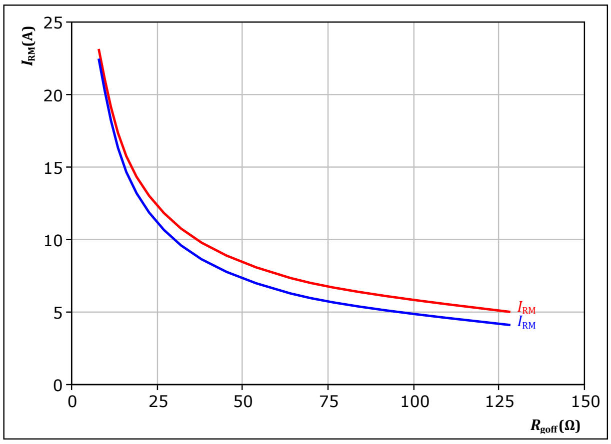
T_j:
— 25 °C
— 125 °C

V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 32 Ω

figure 22. **FWD**

Typical peak reverse recovery current as a function of turn off gate resistor

I_{RM} = f(R_{goff})



With an inductive load at

T_j:
— 25 °C
— 125 °C

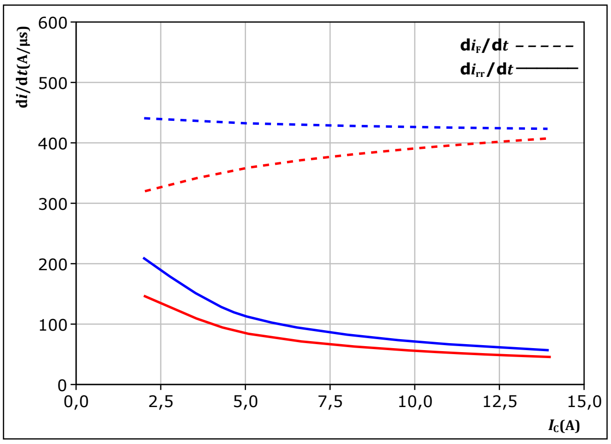
V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 8 A

Inverter Switching Characteristics

figure 23. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

$di_F/dt,\ di_{rr}/dt = f(I_C)$



With an inductive load at

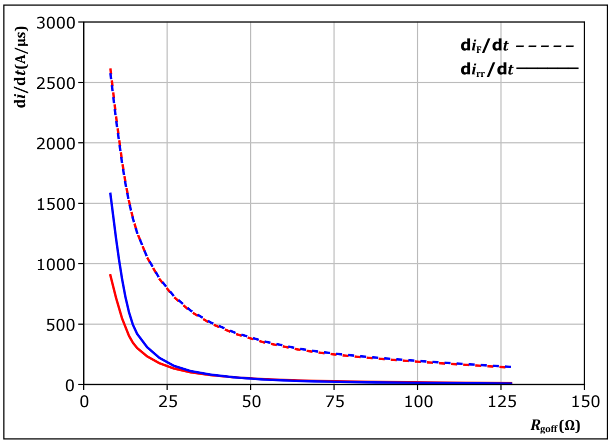
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 32 Ω

T_j: 25 °C, 125 °C

figure 24. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn off gate resistor

$di_F/dt,\ di_{rr}/dt = f(R_{goff})$



With an inductive load at

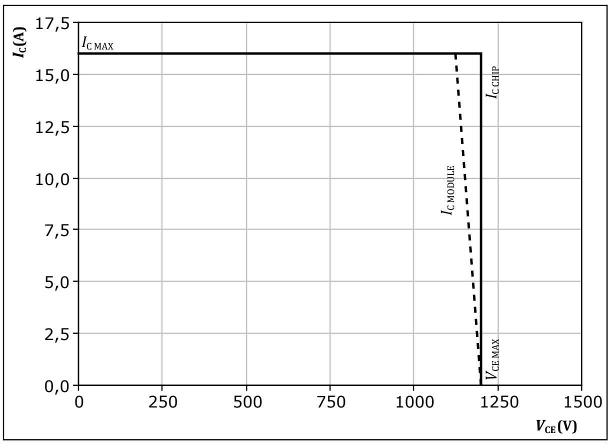
V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 8 A

T_j: 25 °C, 125 °C

figure 25. **IGBT**

Reverse bias safe operating area

$I_C = f(V_{CE})$



At T_j = 125 °C
R_{gon} = 32 Ω
R_{goff} = 32 Ω

Inverter Switching Definitions

figure 26. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} **= integrating time for** E_{off})

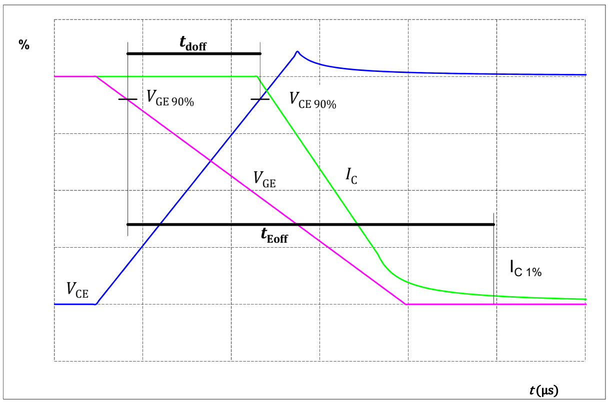


figure 27. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} **= integrating time for** E_{on})

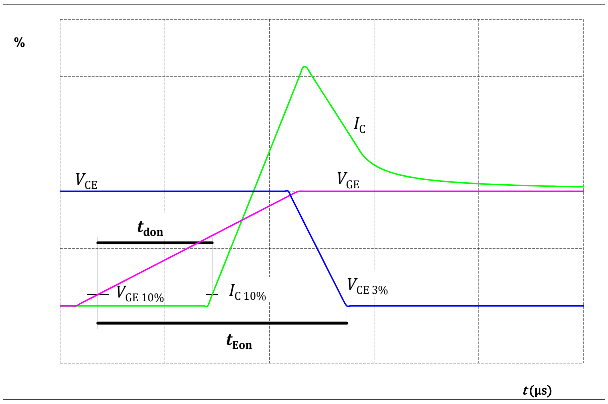


figure 28. **IGBT**

Turn-off Switching Waveforms & definition of t_{f}

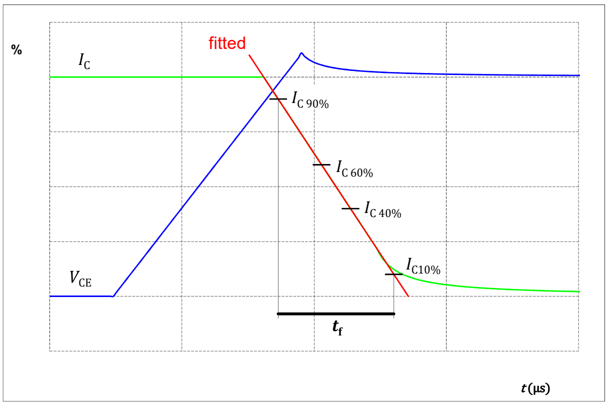
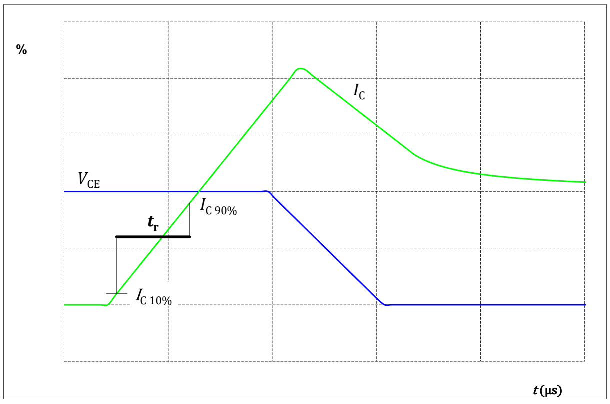


figure 29. **IGBT**

Turn-on Switching Waveforms & definition of t_{r}



Inverter Switching Definitions

figure 30. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

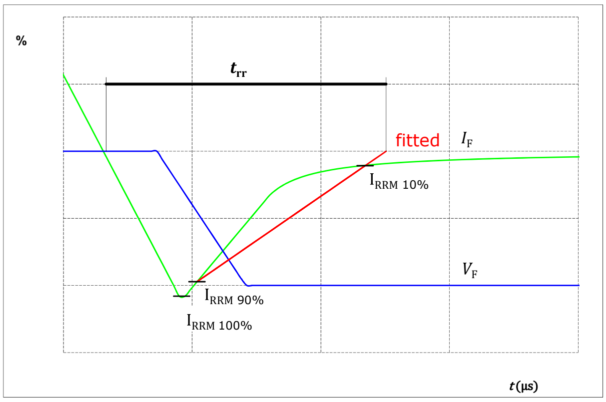
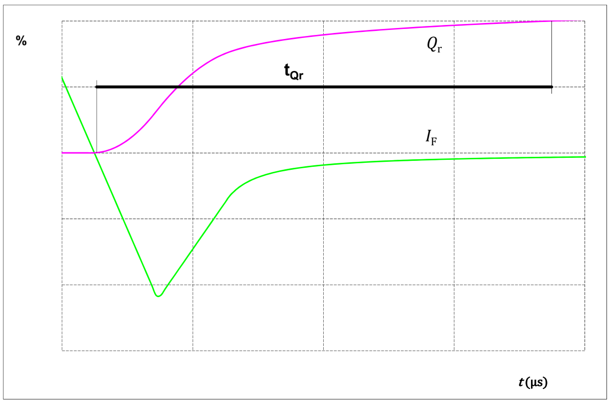


figure 31. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

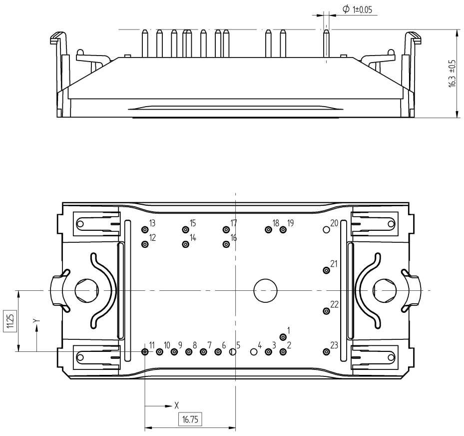
Version	Ordering Code
Without thermal paste	V23990-P849-C48-PM
With thermal paste (5,2 W/mK, PTM6000HV)	V23990-P849-C48-/7/-PM
With thermal paste (3,4 W/mK, PSX-P7)	V23990-P849-C48-/3/-PM

Marking

	**Text**	**VIN**	**Date code**	**Type&Ver**	**UL**	**Lot**	**Serial**
		VIN	WWYY	TTTTTTTVV	UL	LLLLL	SSSS
	Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
		TTTTTTTVV	LLLLL	SSSS	WWYY		

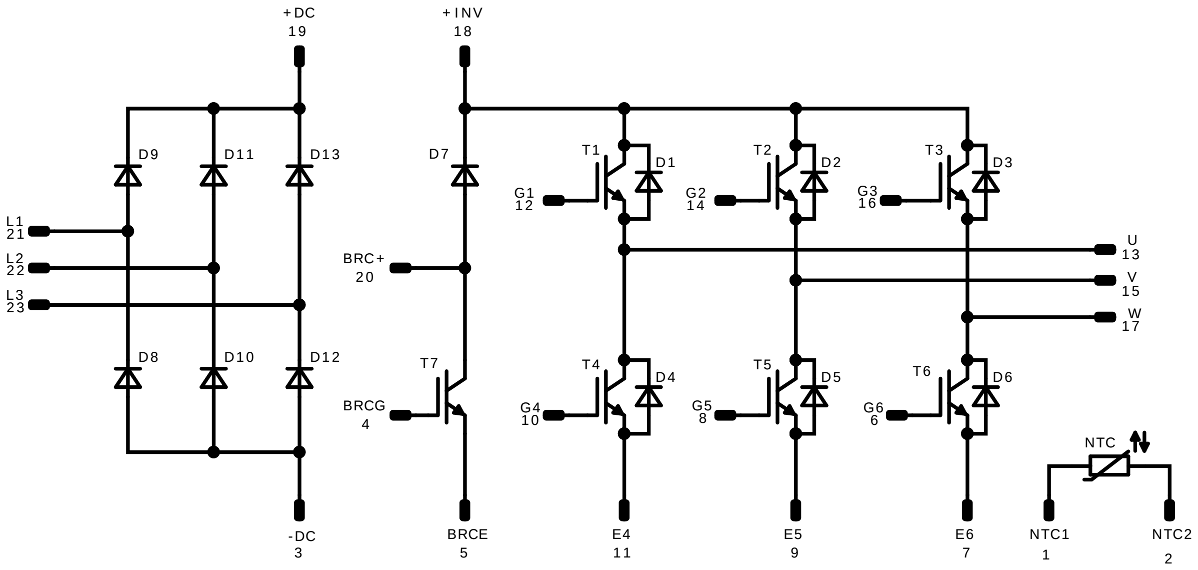
Outline

Pin table [mm]			
Pin	X	Y	Function
1	25,5	2,7	NTC1
2	25,5	0	NTC2
3	22,8	0	-DC
4	not assembled		
5	not assembled		
6	13,5	0	G6
7	10,8	0	E6
8	8,1	0	G5
9	5,4	0	E5
10	2,7	0	G4
11	0	0	E4
12	0	19,8	G1
13	0	22,5	U
14	7,5	19,8	G2
15	7,5	22,5	V
16	15	19,8	G3
17	15	22,5	W
18	22,8	22,5	+INV
19	25,5	22,5	+DC
20	not assembled		
21	33,5	15	L1
22	33,5	7,5	L2
23	33,5	0	L3



Tolerance of pinpositions: ±0.5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T4, T1, T5, T2, T6, T3	IGBT	1200 V	8 A	Inverter Switch	
D1, D4, D2, D5, D3, D6	FWD	1200 V	10 A	Inverter Diode	
D8, D9, D10, D11, D12, D13	Rectifier	1600 V	25 A	Rectifier Diode	
NTC	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
V23990-P849-C48-PM-D9-14	30 Sep. 2021	New Datasheet format, module is unchanged Correct Static values of Inverter Diode, Rectifier Diode Separate datasheet	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.